



N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	I _D max T _A = 25°C		
30V	14mΩ @ V _{GS} = 10V	8.6A		
307	$20m\Omega @ V_{GS} = 4.5V$	7.1A		

Description and Applications

This MOSFET has been designed to minimize the on-state resistance $(R_{DS(ON)})$ and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- Power Management Functions
- DC-DC Converters

Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

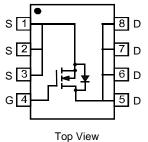
Mechanical Data

Case: SO-8

- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Copper lead frame. Solderable per MIL-STD-202, Method 208 🚳
- Weight: 0.072g (approximate)



Top View



Internal Schematic

Ordering Information (Note 4)

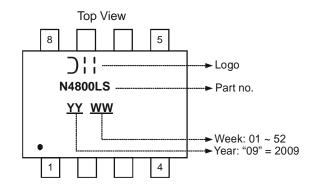
Part Number	Case	Packaging
DMN4800LSS-13	SO-8	2500/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

For packaging details, go to our website at http://www.diodes.com.

Marking Information





Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	30	V
Gate-Source Voltage			V _{GSS}	±25	V
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	T _A = 25°C T _A = 70°C	I _D	8.6 6.3	A
	t<10s	$T_A = 25^{\circ}C$ $T_A = 70^{\circ}C$	I _D	11.8 9.0	A
Maximum Body Diode Forward Current (Note 6)			I _S	2.4	A
Pulsed Drain Current (Note 7)			I _{DM}	50	A

Thermal Characteristics $@T_A = 25^{\circ}C$ unless otherwise specified

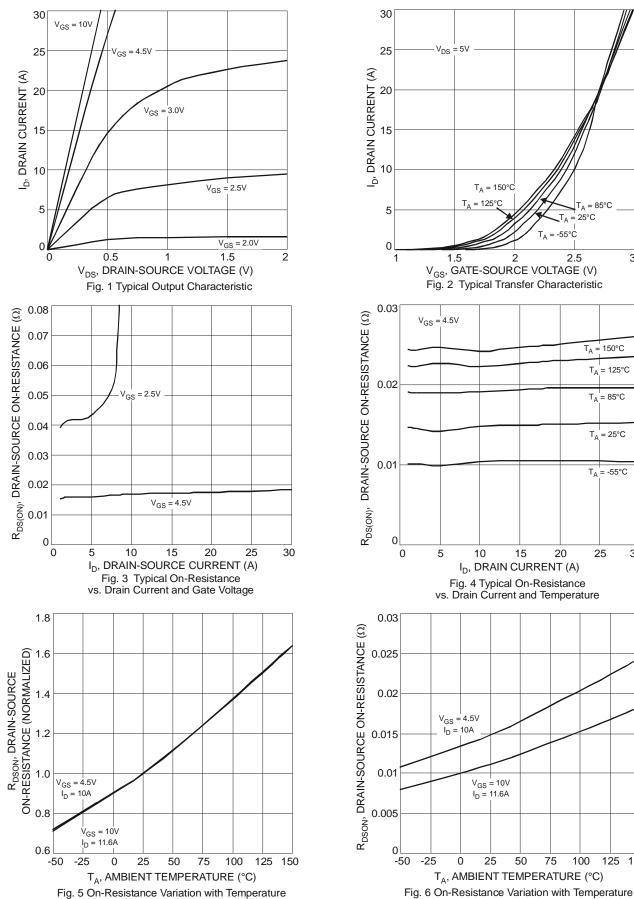
Characteristic	Symbol	Value	Units		
Total Bower Discinction (Nata E)	T _A = 25°C	Р	1.46	W	
Total Power Dissipation (Note 5)	T _A = 70°C	– P _D –	0.9	vv	
Thermal Registeres, Junction to Ambient (Note 5)	Steady state	D	86	°C/W	
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	R _{0JA}	46	C/W	
Total Dower Dissinction (Nate 6)	T _A = 25°C	P	1.7	W	
Total Power Dissipation (Note 6)	T _A = 70°C	PD PD	1.0	vv	
Thermal Desistance Junction to Ambient (Note C)	Steady state		75		
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	R _θ JA	40	°C/W	
Thermal Resistance, Junction to Case (Note 6)		R _{0JC}	15		
Operating and Storage Temperature Range		T _{J.} T _{STG}	-55 to +150	0°	

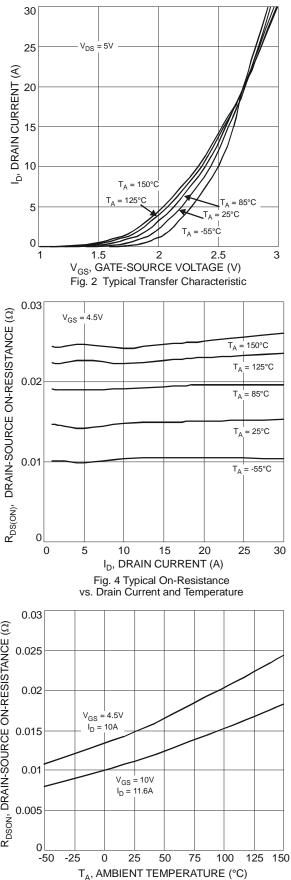
Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	30			V	$V_{GS} = 0V, I_D = 250 \mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Source Leakage	Igss	—	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(th)}	0.8	1.2	1.6	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance	Р		11	14	mΩ	$V_{GS} = 10V, I_{D} = 9A$	
	R _{DS (ON)}	—	14	20		$V_{GS} = 4.5V, I_D = 7A$	
Forward Transconductance	g fs	—	8		S	$V_{DS} = 10V, I_D = 9A$	
Diode Forward Voltage (Note 8)	V _{SD}	_	0.72	0.94	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 9)					÷		
Input Capacitance	Ciss	_	798		pF		
Output Capacitance	Coss	_	128		pF	└ V _{DS} = 10V, V _{GS} = 0V - f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	122	_	pF		
Gate Resistance	R _G	_	1.37		Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge	Qg	_	8.7	_			
Gate-Source Charge	Q _{gs}		1.7		nC	$V_{GS} = 5V, V_{DS} = 15V, I_D = 9A$	
Gate-Drain Charge	Q _{gd}		2.4				
Turn-On Delay Time	t _{d(on)}	_	5.03	_		$\label{eq:VDD} \begin{split} V_{DD} &= 15V, V_{GEN} = 10V, \\ R_L &= 15\Omega, R_G = 6.0\Omega, I_D = 1A \end{split}$	
Rise Time	tr		4.50	_			
Turn-Off Delay Time	t _{d(off)}	_	26.33	_	ns		
Fall Time	t _f	_	8.55	_			

 Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout
Repetitive rating, pulse width limited by junction temperature.
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing. Notes:









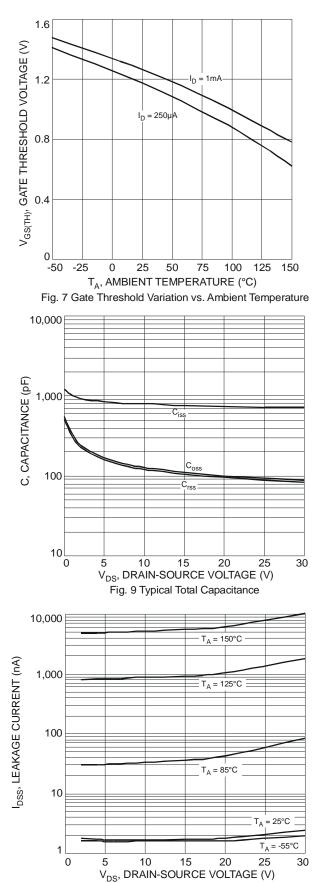
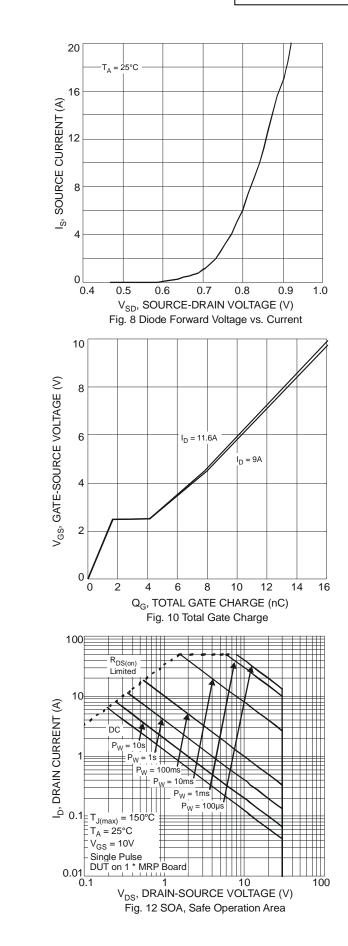
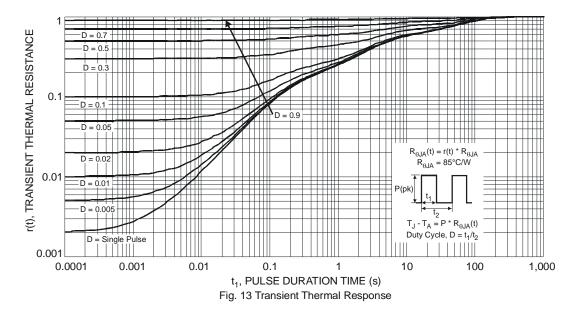


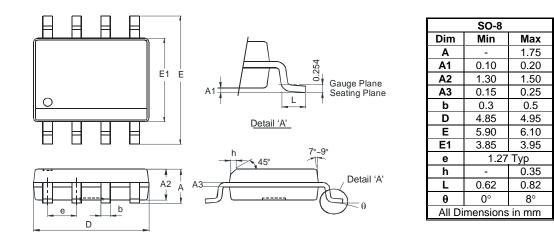
Fig. 11 Typical Leakage Current vs. Drain-Source Voltage



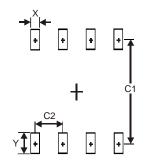




Package Outline Dimensions



Suggested Pad Layout



Dimensions	Value (in mm)
Х	0.60
Y	1.55
C1	5.4
C2	1.27



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